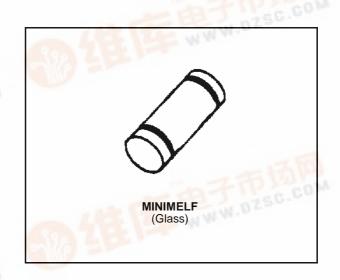


TMMBAT 46

SMALL SIGNAL SCHOTTKY DIODE



General purpose, metal to silicon diode featuring high breakdown voltage low turn-on voltage.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive Peak Reverse Voltage	100	V
IF	Forward Continuous Current	150	mA
I _{FRM}	Repetitive Peak Fordware Current	350	mA
I _{FSM}	Surge non Repetitive Forward Current	750	mA
P _{tot}	Power Dissipation	150	mW
T _{stg} T _j	Storage and Junction Temperature Range	- 65 to + 150 - 65 to + 125	°C °C
TL	Maximum Temperature for Soldering during 1	260	°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th(j-l)}	Junction-leads	300	°C/W



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TMMBAT 46

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol		Test Conditions		Min.	Тур.	Max.	Unit
V_{BR}	T _j = 25°C		$I_R = 100 \mu A$	100			V
V _F *	$T_j = 25^{\circ}C$		$I_F = 0.1 \text{mA}$			0.25	V
	$T_j = 25^{\circ}C$		$I_F = 10mA$			0.45	
	$T_j = 25^{\circ}C$		$I_F = 250 \text{mA}$			1	
I _R *	$T_j = 25^{\circ}C$		$V_{R} = 1.5V$			0.5	μΑ
	$T_j = 60^{\circ}C$					5	
	$T_j = 25^{\circ}C$		$V_R = 10V$			0.8	
	$T_j = 60^{\circ}C$					7.5	
	$T_j = 25^{\circ}C$		$V_R = 50V$			2	
	$T_j = 60^{\circ}C$					15	
	$T_j = 25^{\circ}C$		$V_R = 75V$			5	
	T _j = 60°C					20	

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
С	T _j = 25°C	$V_R = 0V$	f = 1MHz		10		pF
	T _j = 25°C	$V_R = 1V$			6		

^{*} Pulse test: $t_p\!\leq\!300\mu s~\delta\!<\!2\%$.

Figure 1. Forward current versus forward voltage at different temperatures (typical values).

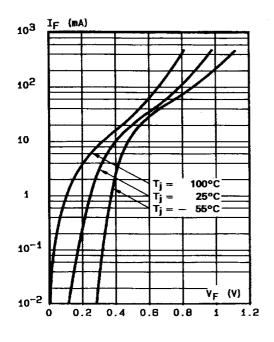


Figure 2. Forward current versus forward voltage (typical values).

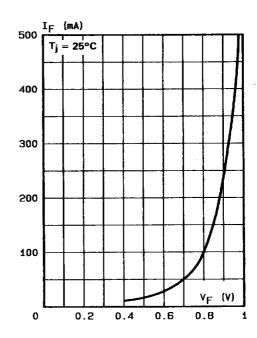


Figure 3. Reverse current versus junction temperature (typical values).

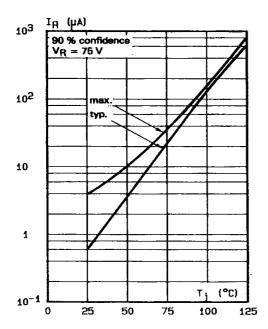


Figure 4. Reverse current versus continuous reverse voltage.

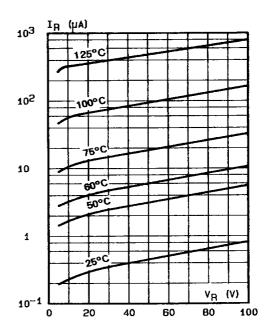
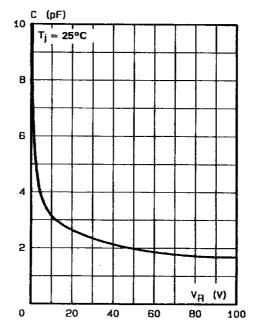
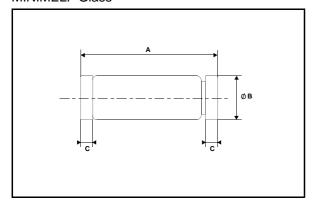


Figure 5. Forward current versus forward voltage (typical values).



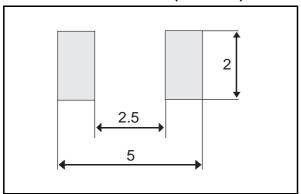
PACKAGE MECHANICAL DATA

MINIMELF Glass



			DIMEN	SIONS		
REF.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	3.30	3.40	3.6	0.130	0.134	0.142
В	1.59	1.60	1.62	0.063	0.063	0.064
С	0.40	0.45	0.50	0.016	0.018	0.020
D		1.50			0.059	

FOOT PRINT DIMENSIONS (Millimeter)



Marking: ring at cathode end. Weight: 0.05g

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